

N-Channel Logic Level Enhancement Mode MOSFET

Description

The MSK 1N3 is a N-channel enhancement-mode

MOSFET.

Features

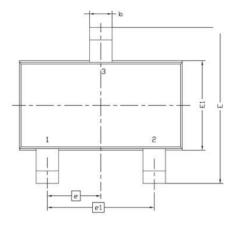
- Low on-resistance
- High ESD
- High speed switching
- Low-voltage drive (4V)
- · Easily designed drive circuits
- · Easy to use in parallel
- RoHS compliant package

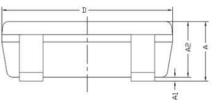
Packing & Order Information

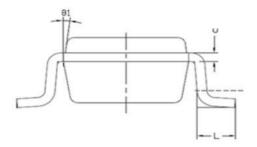
3,000/Reel





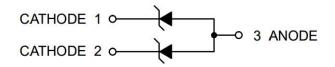






Sumbol	MILLIMETERS		
Symbol	MIN	MAX	
A	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
E	2.6	3	
E1	1.4	1.8	
е	0.95	BSC	
e1	1.9 BSC		
L	0.3	0.6	
θ1	7° NOM		

Graphic symbol





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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Ta=25°C)					
Symbol	Parameter	Value	Unit		
V_{DS}	Drain-Source Voltage	20	V		
V_{GS}	Gate-Source Voltage	±8	V		
I _D	Drain Current -Continuous ($T_A = 25^{\circ}C$)	6	А		
	Drain Current -Continuous (T _A =70°C)	3.6	Α		
I _{DM}	Pulsed Drain Current	22	А		
P _D	Total Power Dissipation (T _A =25°C)	0.83	W		
	Total Power Dissipation (T_A =70°C)	0.3	W		
ls	Continuous Source Current (Diode Conduction) ^a	1	A		
T_{J},T_{STG}	Operating and Storage Temperature Range	-55 to +150	°C		

Thermal Data					
Symbol	Parameter	Max.	Units		
$R_{ extsf{ heta}JA}$	Maximum Junction-to- Ambient ^a (t<=10 sec)	110	°C/W		
$R_{ extsf{ heta}JA}$	Maximum Junction-to- Ambient ^a (Steady State)	150			

Note:

1. Surface Mounted on 1"x1" FR4 Board.

2. Pulse width limited by maximum junction temperature.

Electrical Characteristics

Static					
Symbol	Test Conditions	Min	Тур.	Max.	Units
V _{SD}	$V_{GS} = 0 V$, $I_S = 1 A$		0.7		V
V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	20			V
I _{DSS}	$V_{DS} = 24 V$, $V_{GS} = 0 V$ $V_{DS} = 20 V$, $V_{GS} = 0 V$, $T_j = 125^{\circ}C$			1 30	μA
I _{GSS}	$V_{GS} = \pm 8 V$, $V_{DS} = 0$			±10	nA
I _{D(ON)}	$V_{DS} = 5 V$, $V_{GS} = 4.5 V$	10			A
R _{DS(ON)} *1	$V_{GS} = 2.5 V, I_D = 5 A$ $V_{GS} = 4.5 V, I_D = 6 A$			20 28	mΩ
G _{FS} *1	$V_{DS} = 15 V, I_D = 6 A$		10		S

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
C _{ISS}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0MHz		680		pF
C _{OSS}	Output Capacitance			144		pF
C _{RSS}	Reverse Transfer Capacitance			137		pF



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Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
C _{ISS}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0MHz		680		pF
C _{OSS}	Output Capacitance			144		pF
C _{RSS}	Reverse Transfer Capacitance			137		pF
Q_g	Total Gate Charge	$V_{DS} = 10 V$, $I_D = 6 A$, $V_{GS} = 4.5 V$		13.5		nC
Q_{gs}	Gate-Source Charge			0.9		nC
Q_{gd}	Gate-Drain Charge			5.4		nC
t _{d(on)}	Turn-On Dalay Time	$\begin{split} V_{DD} &= 10 \text{ V} \text{ , } I_D = 1 \text{ A} \text{,} \\ V_{GEN} &= 4.5 \text{ V} \text{ , } R_{GEN} = 6 \Omega \\ R_L &= 10 \Omega \end{split}$		6		ns
t _r	Rise Time			12		ns
t _{d(off)}	Turn-Off Dalay Time			65		ns
tf	Fall Time			35		ns

Notes

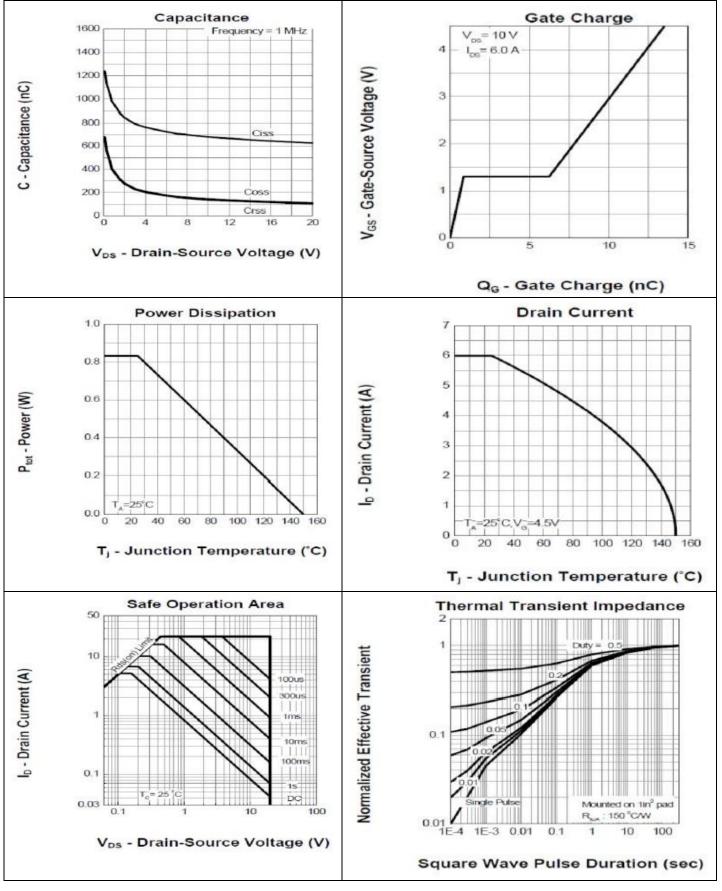
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.



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Characteristics Curves





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